

IN THE SPECIFICATION

Please replace the paragraph at page 1, lines 6-13, with the following rewritten paragraph:

The present invention relates to high-frequency plasma generating apparatuses and high-frequency plasma generating processes, which can be applied to formation of films of semiconductors useful in solar cells cells, thin-film transistors, or the like, such as amorphous silicon, microcrystalline silicon, polycrystalline thin-film silicon, and silicon nitride, or which can be applied to etching of semiconductor films.

Please replace the paragraph at page 1, line 22 to page 2, line 5, with the following rewritten paragraph:

The inside of the reaction chamber 1 shown in Fig. 5 and Fig. 6 is equipped with a ladder-shaped electrode 2 as a discharge electrode and a ground electrode 3. The reaction chamber 1 is made gastight, to which a gas supply pipe and an exhaust pipe (both of which are not shown in the drawings) are open at appropriate positions respectively. Through the gas supply pipe, which communicates with a gas supply source, a gas for film formation is introduced into the reaction chamber 1. The exhaust pipe communicates with the suction side of a vacuum pump. The reaction chamber 1 can be evacuated to an internal pressure of about  $1 \times 10^{-6}$  Torr using this vacuum pump.